

## **Amendments to the Claims**

This listing of claims will replace all prior versions, and listings of claims in the application:

### **Listing of Claims:**

Claims 1-16 (previously canceled)

Claim 17 (currently amended): A method of fabricating an IC chip comprising:

laminating a first insulating layer on a board;

forming an electrode pad on the board, the electrode pad serving as an input/output terminal;

laminating a second insulating layer over the board and the electrode pad;

forming a first resist pattern on the second insulating layer at a region other than a part of the electrode pad;

etching and removing the second insulating layer using the first resist pattern as a mask, thereby defining a first opening in the second insulating layer on the electrode pad;

filling the first opening with a conductive material layer made of a conductive material;

laminating a third insulating layer over the second insulating layer and the

conductive material layer;

forming a second resist pattern on the third insulating layer at a region other than a region of the conductive material layer;

etching and removing the third insulating layer using the second resist pattern as a mask, thereby defining a second opening in the third insulating layer at the region of the conductive material layer;

filling the second opening with a metal layer made of an electric connection material; [[and]]

etching and removing the third insulating layer and the second insulating layer after said filling the second opening; and

forming a filling insulating material on the first insulating layer and the electrode pad after said etching and removing the third insulating layer and the second insulating layer, to surround sidewalls of the conductive material layer and the metal layer.

Claim 18 (original): The method of fabricating an IC chip according to claim 17, wherein the electric connection material is molten solder.

Claim 19 (canceled)

Claim 20 (previously canceled)

Claim 21 (canceled)

Claims 22-24 (previously canceled)

Claim 25 (previously presented): The method of fabricating an IC chip according to claim 17, wherein the second resist pattern is formed so that the metal layer filled in the second opening is wider than the conductive material layer filled in the first opening.

Claim 26 (previously presented): The method of fabricating an IC chip according to claim 17, wherein the second resist pattern is formed so that the metal layer filled in the second opening is narrower than the conductive material filled in the first opening.

Claim 27 (currently amended): The method of fabricating an IC chip according to claim 17, wherein the second resist pattern is formed so that a width of the metal layer filled in the second opening is substantially the same as a width of the conductive material layer in the ~~second~~ first opening.

Claim 28 (previously presented): The method of fabricating an IC chip according to claim 17, further comprising:

placing the board over a printed board after said etching and removing the third insulating layer and the second insulating layer, the electrode pad being aligned with a

pad formed on the printed board; and

heating the electric connection material to electrically connect the electrode pad with the pad formed on the printed board.

Claim 29 (previously presented): The method of fabricating an IC chip according to claim 28, wherein the electric connection material is solder.

Claims 30-33 (canceled)